



JIANGSU CHANGJIANG ELECTRONICS INDUSTRIAL CO., LTD

SOT-23 Plastic-Encapsulate Transistors

S9016LT1 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

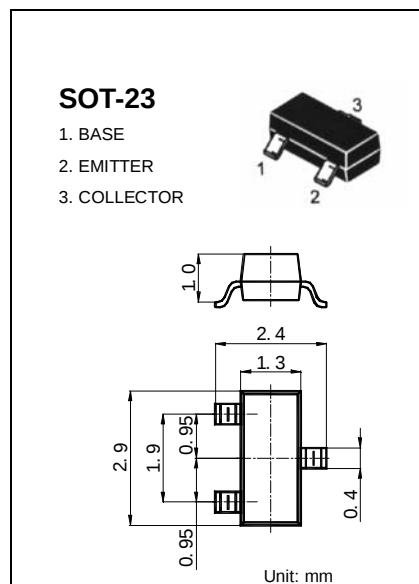
I_{CM} : 0.025 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$			0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE}=5V, I_C=1mA$	70		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.3	V
Transition frequency	f_T	$V_{CE}=5V, I_C=1mA$ $f=100MHz$	300			MHz

DEVICE MARKING

S9016LT1= Y6